

Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	

Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1.5	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V$ $R_L=33$	- -	MAX.	10	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				30	
$I_H$	$I_T=100mA$		MAX.	15	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$		MIN.	100	V/ $\mu s$
(dI/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =10V/ $\mu s$ , $T_j=125$		MIN.	3	A/ms
$t_{on}$	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5	$\mu s$
$t_{off}$				25	

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=11A$ $t_p=380\mu s$	$T_j=25$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.82	V
$R_D$	Dynamic resistance	$T_j=125$	45	m
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	10	$\mu A$
$I_{RRM}$		$T_j=125$	1	mA

**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.8	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W



# JST08F-



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**FIG.1:** Maximum on-state current



**FIG.2:** RMS on-state current versus case temperature





**ORDERING INFORMATION**

Order code	Voltage V <sub>DRM</sub> /V <sub>RRM</sub> (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
<b>JST08F-1200SW</b>	<b>1200</b>	<b>10</b>	<b>TO-220F(Ins)</b>	<b>50</b>	<b>Tube</b>

**Document Revision History**

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated
Oct.13, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

**PACKAGE MECHANICAL DATA**



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